

VERSION SHOWING THE CHANGES TO THE CLAIMS

This listing replaces all prior listings of the claims.

Claims 1 and 2, canceled.

3 (Currently amended). A method for the production of an organic electronic component, comprising:

forming in which a homogeneous single organic semiconductive layer into two different, but adjacent first and second functional regions layers are produced in a single process step, having the same chemical properties, but the different first and second functional regions exhibiting respective semiconductive and conductive different electrical properties, by the forming step comprising converting the second region part of a the semiconductive functional layer into a another different conductive functional region layer by modification of the material by partial reaction of the semiconductive layer in the second region;

the forming step including forming the second region by converting the semiconductive functional layer in the second region in a controlled manner by printing the second region with a composition for implementing said partial reaction.

4 (Currently amended). The method as claimed in claim 3, in which the conductive functional second region forms electrodes and/or conductor tracks, the electrodes and/or conductor tracks and the semiconductive functional first region layer being are produced with structuring in a one process printing step of the single organic and in one

functional layer.

5 (Currently amended). The method as claimed in claim 3 wherein ~~one of the functional layers is a semiconductive layer, in which a conductive structure is introduced in a controlled manner into the semiconductive functional layer by partial covering and~~ the partial reaction is conducted by treatment of the uncovered second region[[s]] with a redox composition.

6 (Currently amended). The method as claimed in claim 3, in which ~~one of the functional layers is a semiconductive layer and~~ the step of forming the second region includes covering the single organic semiconductive layer first region with is covered by a photoresist while exposing the first region.

7 (Currently amended) The method as claimed in claim 3 5, ~~in which the redox composition is partially applied to the semiconductive functional layer by printing wherein the step of forming a homogeneous single organic semiconductive layer into two different, but adjacent first and second functional regions comprises forming the single layer into a plurality of at least said adjacent second functional regions.~~

8 (Currently amended). The method as claimed in claim 3 , in which the partial reaction comprises performing a time-stable partial oxidation of the semiconductive

functional layer in the second region with ~~is carried out by~~ an oxidizing agent.

9 (Currently amended). The method as claimed in claim 4, in which the a conductive property structure is introduced in a controlled manner by ~~into the semiconductive functional layer by partial covering and~~ treatment of the ~~uncovered~~ second region with a redox composition.

10 (Currently amended). The method as claimed in claim 4 in which the semiconductive layer first region is formed by covering the semiconducting layer first region with ~~is covered by~~ a photoresist.

11 (Currently amended). The method as claimed in claim 5 in which the semiconductive layer first region is formed by covering the semiconducting layer first region with ~~is covered by~~ a photoresist.

12 (Currently amended). The method as claimed in claim 3 wherein ~~one of the functional layers is a semiconductive functional layer in which the printing of the composition for the partial reaction comprises printing~~ a redox composition ~~is partially applied to onto~~ the semiconductive functional layer second region by printing.

Claim 13, canceled.

14. (Currently amended). The method as claimed in claim 6 wherein the printing of the composition comprises applying in which a redox composition is ~~partially applied~~ to the exposed second region of the semiconductive functional layer by printing.

15 (Currently ame0nded). The method as claimed in claim 4 wherein the printing the second region with a composition for implementing said partial reaction in which comprises performing a time-stable partial oxidation of the semiconductive functional layer second region with ~~is carried out by~~ an oxidizing agent.

16 (Currently amended). The method as claimed in claim 5 wherein the printing the uncovered second region with a composition for implementing said partial reaction comprises performing in which a time-stable partial oxidation of the semiconductive functional layer second region with ~~is carried out by~~ an oxidizing agent.

17 (Currently amended). The method as claimed in claim 6 wherein the printing the exposed second region with a composition for implementing said partial reaction comprises performing in which a time-stable partial oxidation of the semiconductive functional layer second region with ~~is carried out by~~ an oxidizing agent.

18 (Currently amended) The method as claimed in claim 3 7 ~~in which a time-stable~~

~~partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent~~ wherein the step of forming a homogeneous single organic semiconductive layer into two different, but adjacent first and second functional regions comprises forming the single layer into a plurality of said adjacent first and second functional regions .

What this claim called for was a semiconductor layer which is partially covered in a controlled manner wherein the uncovered region is treated with a redox composition. This treatment made the uncovered region electrically conductive as compared to the covered region which remains a semiconductor. Thus a single semiconductor layer is made both semiconductive and conductive by the treatment of the uncovered exposed region of the semiconductor layer. Obviously the semiconductor layer is a single layer of semiconductor material and claim 5 thus converted a portion of the semiconductor material of the single layer into an electrically conductive region. Thus the single layer after such conversion comprises both an electrical semiconductor region and an electrically conductive region, which is achieved by treatment of the single semiconductor layer.

Amended claim 3 calls for similar method steps in somewhat different form, and does not use the term redox and has other differences. Claim 3 calls for converting the semiconductor second region into a conductive functional region by partial reaction of the semiconductive functional layer in the second region. Claim 3 also forms the single layer from a homogeneous single organic semiconductor layer into the two different adjacent first and second functional regions exhibiting semiconductive and conductive electrical properties. Thus substantively, the issues remain substantially similar as to converting a portion of a semiconductor region into a conductive region. However, the Chondross reference is foreign to these claims as there is no disclosure therein of a single organic semiconductor layer converted partially into a conductor as